



ZVP2106G

60V P-CHANNEL ENHANCEMENT MODE VERTICAL DMOSFET

Product Summary

BV _{DSS}	R _{DS(on)}	I _D T _A = +25°C
-60V	5Ω @ V _{GS} = -10V	-450mA

Description

This MOSFET is designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Load Switch
- **DC-DC Converters**

Features and Benefits

- Low On-Resistance
- Fast Switching Speed
- Lead-Free Finish; RoHS compliant (Note 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

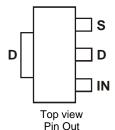
Mechanical Data

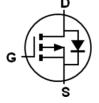
- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish
- Weight: 0.112 grams (Approximate)





Top View





Equivalent Circuit

Ordering Information (Note 4)

Product	Case	Quantity per reel
ZVP2106GTA	SOT223	1,000

Note:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

SOT223 ZVP 2106

ZVP2106 = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Year (ex: 5 = 2015) WW or $\overline{W}W = Week (01 - 53)$

March 2015



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V_{DS}	-60	V
Gate Source Voltage	V _{GSS}	±20	V
Continuous Drain Current	I _D	-450	M A
Pulsed Drain Current	I _{DM}	-4	А

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Power Dissipation	P _{TOT}	2	W
Storage Temperature Range	T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

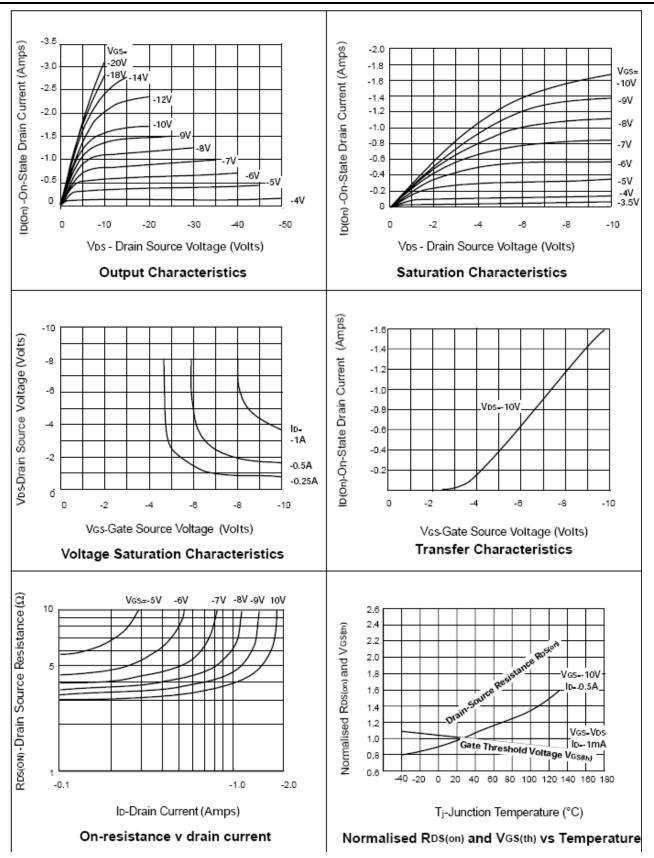
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Static Characteristics						•
Drain-Source Breakdown Voltage	BV _{DSS}	-60	_	_	V	$I_D = -1 \text{mA}, V_{GS} = 0 \text{V}$
Gate-Source Threshold Voltage	V _{GS(th)}	-1.5	_	-3.5	V	$I_D = -1 \text{mA}, V_{DS} = V_{GS}$
Gate-Body Leakage	I _{GSS}	_	_	20	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
				-0.5	μA	$V_{DS} = -60V, V_{GS} = 0V$
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-100	μA	$V_{DS} = -48V, V_{GS} = 0V,$ T= +125°C (Note 6)
On-State Drain Current (Note 5)	I _{D(on)}	-1	_	_	Α	V _{DS} = -18V, V _{GS} = -10V
Static Drain-Source On-State Resistance (Note 5)	R _{DS(on)}	_	_	5	Ω	$V_{GS} = -10V, I_D = -500mA$
Forward Transconductance (Notes 5 & 6)	g fS	150	_	_	mS	$V_{DS} = -18V, I_D = -500mA$
Dynamic Characteristics (Note 6)				-		•
Input Capacitance	C _{iss}	_	_	100		
Common Source Output Capacitance	Coss	_	_	60	pF	$V_{DS} = -18V, V_{GS} = 0V, f=1MHz$
Reverse Transfer Capacitance	C _{rss}	_	_	20		
Turn-On Delay Time (Note 7)	t _{d(on)}	_	_	7		
Rise Time (Note 7)	t _r	_	_	5		\/ 40\/ 500m ^
Turn-Off Delay Time (Note 7)	t _{d(off)}	_	_	12	ns $V_{DD} = -18V$, $I_D = -500$ mA	
Fall Time (Note 7)	f _f	_		15		

Notes:

- 5. Measured under pulsed conditions. Width=300 μ s. Duty cycle \leq 2%.
- 6. Sample Test 7. Switching times measured with 50Ω source impedance and <5ns rise time on a pulse generator.

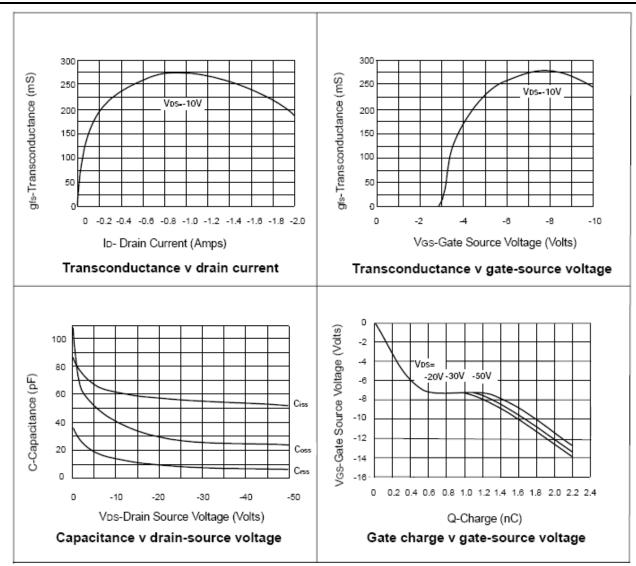


Typical Characteristics





Typical Characteristics (cont.)

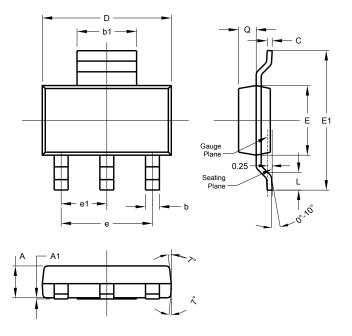


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Package Outline Dimensions

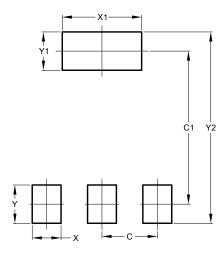
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223				
Dim	Min	Max	Тур	
Α	1.55	1.65	1.60	
A1	0.010	0.15	0.05	
b	0.60	0.80	0.70	
b1	2.90	3.10	3.00	
С	0.20	0.30	0.25	
D	6.45	6.55	6.50	
Е	3.45	3.55	3.50	
E1	6.90	7.10	7.00	
е	-	-	4.60	
e1	-	-	2.30	
L	0.85	1.05	0.95	
Q	0.84	0.94	0.89	
All Dimensions in mm				

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
V2	8 00



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